

Title (en)  
OPTICAL SEMICONDUCTOR DIODE

Title (de)  
OPTISCHE HALBLEITERDIODE

Title (fr)  
DIODE OPTIQUE A SEMI-CONDUCTEUR

Publication  
**EP 1086498 A1 20010328 (DE)**

Application  
**EP 00914057 A 20000302**

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Abstract (en)  
[origin: WO0060675A1] The invention relates to an optical semiconductor diode (1) in which at least one intermediate layer (4) is positioned between an epitaxial layer stack (2) on a surface region (11) of a substrate (10) and said surface region. The intermediate layer contacts the surface region on its flat side such that it partly covers same and partly leaves it exposed and reflects a part (32) of a radiation (30) generated in the layer stack in the direction of the surface region.

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